

SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 3, line 12 with:

Referring to the graph of Fig.25, when the reflectance of the low reflective film 8 is controlled within $6\% \pm 1\%$, it is seen that the thickness of the low reflective film 8 must be controlled with an accuracy of $\pm 1\%$, i.e., nearly ± 3 nm with respect to the design value of thickness $da = 318.9$ nm. Such an accuracy of thickness is difficult to obtain by means of vacuum evaporation or sputtering which is generally used for forming an optical thin film, resulting in a lower yield of manufacturing a semiconductor laser.